Zibo Seno Electronic Engineering Co., Ltd.

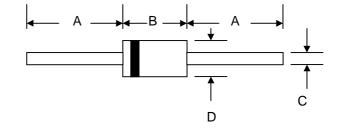


SR320 – SR3200 🚱 🏹

3.0A SCHOTTKY BARRIER DIODE

Features

- Schottky Barrier Chip
- Guard Ring Die Construction for Transient Protection
- High Current Capability
- Low Power Loss, High Efficiency
- High Surge Current Capability
- For Use in Low Voltage, High Frequency Inverters, Free Wheeling, and Polarity Protection Applications



Mechanical E	Data

- Case: DO-201AD, Molded Plastic
- Terminals: Plated Leads Solderable per MIL-STD-202, Method 208
- Polarity: Cathode Band
- Weight: 1.2 grams (approx.)
- Mounting Position: Any
- Marking: Type Number
- Lead Free: For RoHS / Lead Free Version

DO-201AD Min Dim Max 24.5 Α 7.20 9.50 в С 1.10 1.30 D 5.00 5.60 All Dimensions in mm

Maximum Ratings and Electrical Characteristics @T_A=25°C unless otherwise specified

Single Phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

Characteristic	Symbol	SR320	SR330	SR340	SR350	SR360	SR380	SR3100	SR3150	SR3200	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	Vrrm Vrwm Vr	20	30	40	50	60	80	100	150	200	V
RMS Reverse Voltage	VR(RMS)	14	21	28	35	42	56	70	105	140	V
Average Rectified Output Current $@T_L = 95^{\circ}C$ (Note 1)	lo	3.0								А	
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)	IFSM	80								A	
Forward Voltage $@I_F = 3.0A$	Vfm	0.55			0	.70	0 0.85		0	0.90	
Peak Reverse Current $@T_A = 25^{\circ}C$ At Rated DC Blocking Voltage $@T_A = 100^{\circ}C$	I RM	0.1 0.05 20 10							mA		
Typical Junction Capacitance (Note 2)	Cj	250								pF	
Typical Thermal Resistance (Note 1)	RθJA	20									°C/W
Operating and Storage Temperature Range	Tj, Ts⊤g	-55 to +150									°C

Note: 1. Valid provided that leads are kept at ambient temperature at a distance of 9.5mm from the case.

2. Measured at 1.0 MHz and applied reverse voltage of 4.0V D.C.

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